

High Voltage Standard Rectifier

$$V_{RRM} = 2200\text{ V}$$

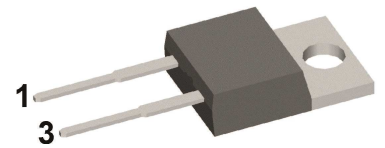
$$I_{FAV} = 30\text{ A}$$

$$V_F = 1.24\text{ V}$$

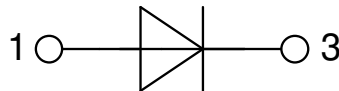
Single Diode

Part number

DNA30E2200PA



Backside: anode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

Applications:

- Diode for main rectification
- For single and three phase bridge configurations

Package: TO-220

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Disclaimer Notice

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.



Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage					2300	V
V_{RRM}	max. repetitive reverse blocking voltage					2200	V
I_R	reverse current	$V_R = 2200$ V		$T_{VJ} = 25^\circ\text{C}$		40	μA
		$V_R = 2200$ V		$T_{VJ} = 150^\circ\text{C}$		1.5	mA
V_F	forward voltage drop	$I_F = 30$ A		$T_{VJ} = 25^\circ\text{C}$		1.26	V
		$I_F = 60$ A				1.53	V
		$I_F = 30$ A		$T_{VJ} = 150^\circ\text{C}$		1.24	V
		$I_F = 60$ A				1.63	V
I_{FAV}	average forward current	$T_C = 140^\circ\text{C}$		$T_{VJ} = 175^\circ\text{C}$		30	A
		rectangular	d = 0.5				
V_{FO}	threshold voltage			$T_{VJ} = 175^\circ\text{C}$		0.83	V
r_F	slope resistance					13.4	m Ω
						} for power loss calculation only	
R_{thJC}	thermal resistance junction to case					0.7	K/W
R_{thCH}	thermal resistance case to heatsink				0.5		K/W
P_{tot}	total power dissipation			$T_C = 25^\circ\text{C}$		210	W
I_{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		370	A
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		400	A
		t = 10 ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		315	A
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		340	A
I^2t	value for fusing	t = 10 ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		685	A ² s
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		665	A ² s
		t = 10 ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		495	A ² s
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		480	A ² s
C_J	junction capacitance	$V_R = 700$ V; f = 1 MHz		$T_{VJ} = 25^\circ\text{C}$		7	pF



Package TO-220			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			35	A
T_{VJ}	virtual junction temperature		-55		175	°C
T_{op}	operation temperature		-55		150	°C
T_{stg}	storage temperature		-55		150	°C
Weight				2		g
M_D	mounting torque		0.4		0.6	Nm
F_C	mounting force with clip		20		60	N

Product Marking



Part description

- D = Diode
- N = High Voltage Standard Rectifier
- A = (>= 2000V)
- 30 = Current Rating [A]
- E = Single Diode
- 2200 = Reverse Voltage [V]
- PA = TO-220AC (2)

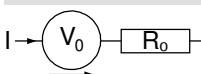
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DNA30E2200PA	DNA30E2200PA	Tube	50	507762

Similar Part	Package	Voltage class
DNA30E2200PZ	TO-263AB (D2Pak) (2HV)	2200
DNA30EM2200PZ	TO-263AB (D2Pak) (2HV)	2200
DNA30E2200FE	i4-Pac (2HV)	2200
DNA30E2200IY	TO-262 (2HV) (I2PAK)	2200

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 175^{\circ}C$



Rectifier

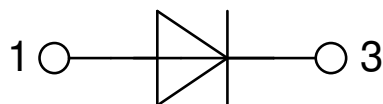
$V_{0\ max}$	threshold voltage	0.83	V
$R_{0\ max}$	slope resistance *	10.2	mΩ



Outlines TO-220



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
C	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
e	5.08	BSC	0.200	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
ØP	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125



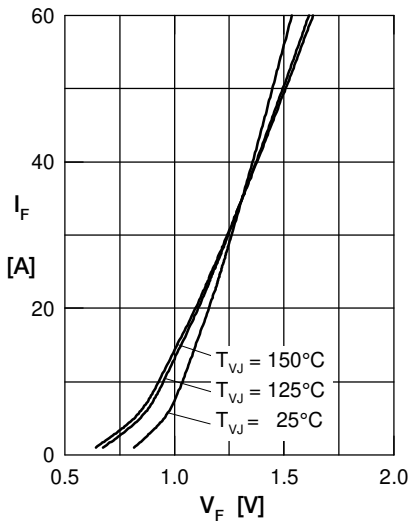
Rectifier


Fig. 1 Forward current versus voltage drop per diode

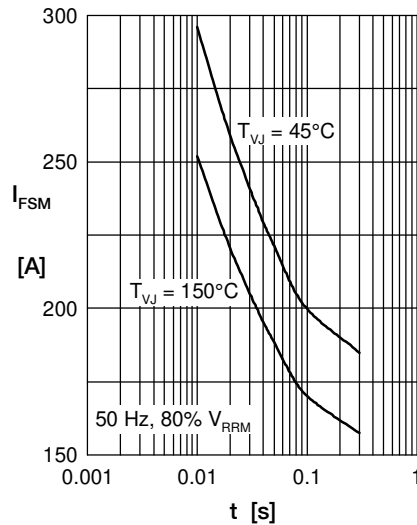


Fig. 2 Surge overload current

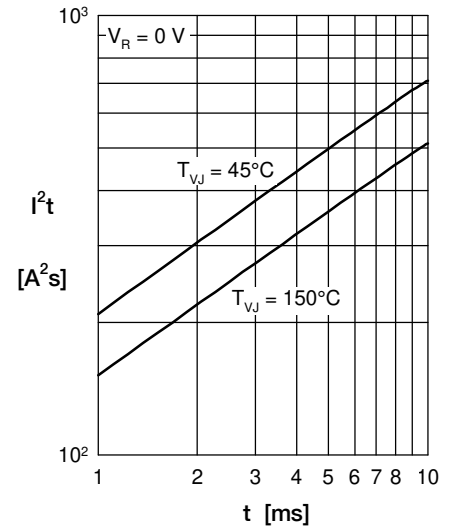
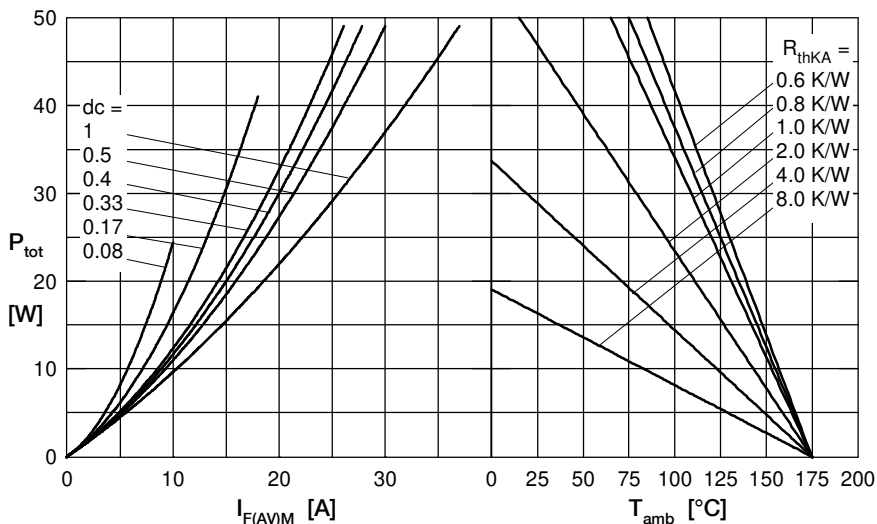

 Fig. 3 I^2t versus time per diode


Fig. 4 Power dissipation versus direct output current and ambient temperature

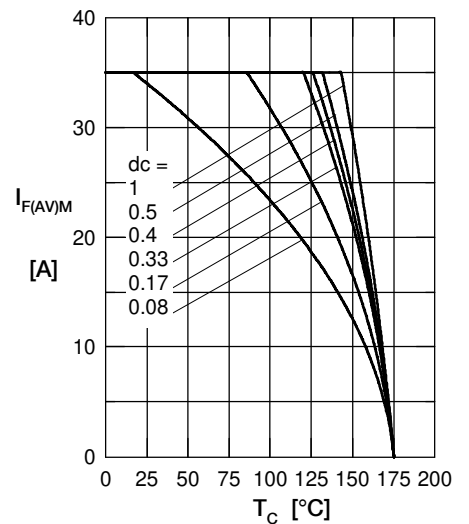


Fig. 5 Max. forward current versus case temperature

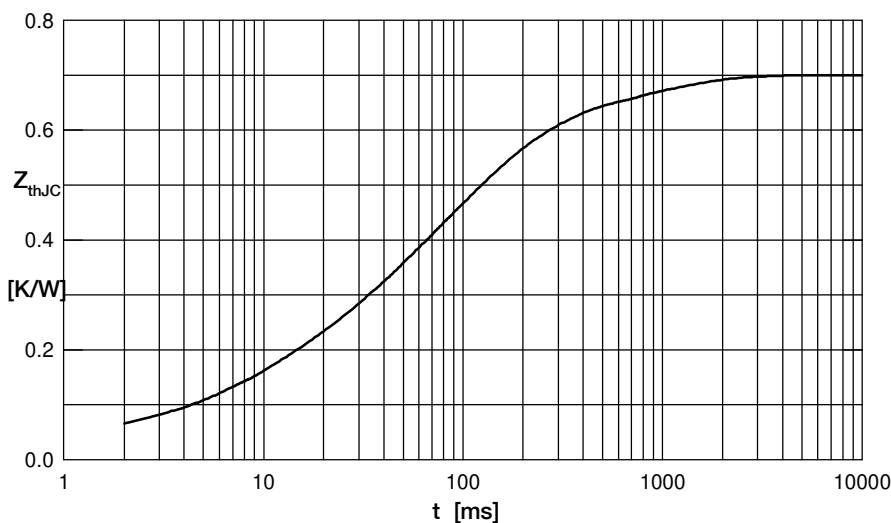


Fig. 6 Transient thermal impedance junction to case

 Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.03	0.0003
2	0.072	0.0065
3	0.131	0.027
4	0.367	0.105
5	0.1	0.8